



國立交通大學

NATIONAL CHIAO-TUNG UNIVERSITY

Semiconductor Power Devices

Wednesday, Dec. 26, 2018 13:00~17:15

國立交通大學 電子資訊研究大樓 201室
MIRC Building, 2nd Floor Room 201, NCTU

Featured Keynote and Plenary Speakers



Ian Chan
(Hermes-Epitek)



M. Kato
(Nagoya Inst of Tech)



Tian-Li Wu
(NCTU)



Y. Daigo
(NuFlare Technology)



Chih-Fang Huang
(NTHU)

Abstract:

For next-generation power devices, wide band-gap semiconductors have great potential as excellent materials with high electricity and reducing power loss. Recently gallium nitride (GaN) and silicon carbide (SiC) devices have been studied and developed intensively, which are expected to achieve energy saving and miniaturization in various areas such as EV, electric trains, electric appliances and power transmission systems.

In this seminar, the future trends and prospects of advanced wide-gap power devices will be addressed. The structure and its application will be also explained in detail, including crystallization and manufacturing technologies.

(Moderator: H. S. Momose)

The organizer: National Chiao Tung University

The co-organizer: College of Electrical and Computer Engineering (ECE), NCTU
International College of Semiconductor Technology (ICST), NCTU